



RECTRON

SEMICONDUCTOR

TECHNICAL SPECIFICATION

1N4150

1N4150 SIGNAL DIODE

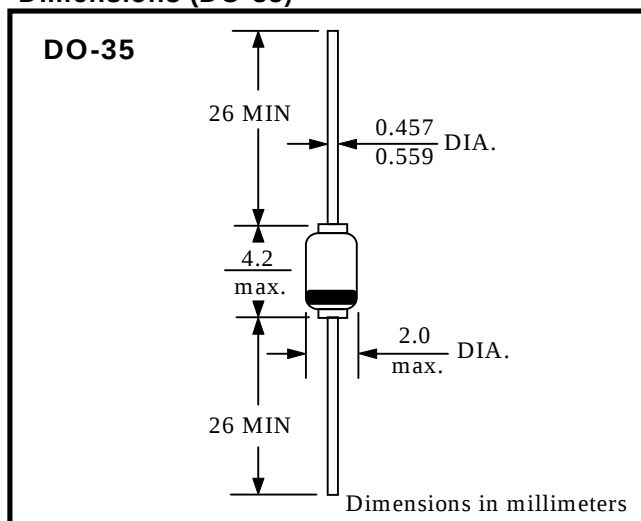
Absolute Maximum Ratings (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	50	V
Reverse Recovery Time	trr	4	ns
Power Dissipation 3.33mW/°C (25°C)	P	500	mW
Forward Current	IF	200	mA
Junction Temp.	Tj	-65 to 200	°C
Storage Temp.	Tstg	-65 to 200	°C

Mechanical Data

Items	Materials
Package	DO-35
Case	Hermetically sealed glass
Lead/Finish	Double stud/Solder Plating
Chip	Glass Passivated

Dimensions (DO-35)



Electrical Characteristics (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Breakdown Voltage IR= 5.0uA	BV	50	V
Peak Forward Surge Current PW= 1sec.	IFsurge	1.0	A
Maximum Forward Voltage IF= 200mA	VF	1.0	V
Maximum Reverse Current VR= 50V VR= 20V, Tj= 150°C	IR	0.10 100	uA
Maximum Junction Capacitance VR= 0, f= 1 MHz	Cj	2.5	pF
Max Reverse Recovery Time IF= -IR= 10-200mA, to 0.1 IF	trr	4	ns